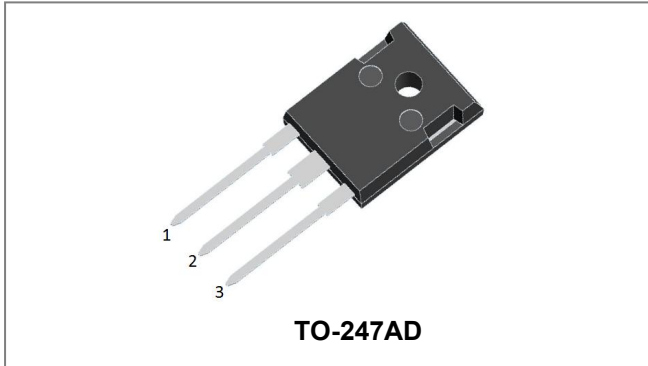


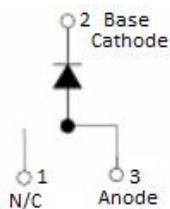
## SDURS30Q60WT ULTRAFAST RECTIFIER



### Applications:

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

### Circuit Diagram



### Features:

- Ultra-Fast switching
- High current capability
- Low reverse leakage current
- High surge current capability
- Terminals finish: 100% Pure Tin
- This is a Pb - free device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	$V_{RRM}$	-	600	V
Working Peak Reverse Voltage	$V_{RWM}$			
DC Blocking Voltage	$V_R$			
Average Rectified Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_c=105^\circ\text{C}$ , rectangular wave form	30	A
Peak One Cycle Non-Repetitive Surge Current	$I_{FSM}$	8.3ms, Half Sine pulse	200	A

**Electrical Characteristics:**

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	$V_{F1}$	@ 30A, Pulse, $T_J = 25^\circ\text{C}$	1.56	1.80	V
	$V_{F2}$	@ 30A, Pulse, $T_J = 125^\circ\text{C}$	1.40	1.60	V
	$V_{F3}$	@ 30A, Pulse, $T_J = 150^\circ\text{C}$	1.34	-	V
Reverse Current*	$I_{R1}$	@ $V_R = \text{rated } V_R, T_J = 25^\circ\text{C}$	0.02	10	$\mu\text{A}$
	$I_{R2}$	@ $V_R = \text{rated } V_R, T_J = 125^\circ\text{C}$	0.006	1	mA
	$I_{R2}$	@ $V_R = \text{rated } V_R, T_J = 150^\circ\text{C}$	0.025	-	mA
Reverse Recovery Time	$t_{rr}$	$I_F = 500\text{mA}, I_R = 1\text{A}, \text{ and } I_{rm} = 250\text{mA}, T_J = 25^\circ\text{C}$	32	40	ns
Reverse Recovery Time	$t_{rr}$	$I_F = 30\text{A}, diF/dt = -200\text{A}/\mu\text{s}$ $V_R = 400\text{V}, T_J = 25^\circ\text{C}$	78	-	ns
Reverse Recovery Charge	$Q_{rr}$		94	-	nC
Reverse Recovery Current	$I_{RRM}$		2.4	-	A
Reverse Recovery Time	$t_{rr}$	$I_F = 30\text{A}, diF/dt = -200\text{A}/\mu\text{s}$ $V_R = 400\text{V}, T_J = 125^\circ\text{C}$	136	-	ns
Reverse Recovery Charge	$Q_{rr}$		435	-	nC
Reverse Recovery Current	$I_{RRM}$		6.4	-	A
Reverse Recovery Time	$t_{rr}$	$I_F = 1\text{A}, diF/dt = -100\text{A}/\mu\text{s}$ $V_R = 30\text{V}, T_J = 25^\circ\text{C}$	30	-	ns
Reverse Recovery Charge	$Q_{rr}$		26	-	nC
Reverse Recovery Current	$I_{RRM}$		2	-	A
Reverse Recovery Time	$t_{rr}$	$I_F = 1\text{A}, diF/dt = -100\text{A}/\mu\text{s}$ $V_R = 30\text{V}, T_J = 125^\circ\text{C}$	65	-	ns
Reverse Recovery Charge	$Q_{rr}$		121	-	nC
Reverse Recovery Current	$I_{RRM}$		4	-	A

\* Pulse width < 300  $\mu\text{s}$ , duty cycle < 2%

**Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	$T_J$	-	-55 to +175	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-	-55 to +175	$^\circ\text{C}$
Typical Thermal Resistance Junction to Case	$R_{\theta JC}$	DC operation	1.15	$^\circ\text{C}/\text{W}$
Approximate Weight	wt	-	6.28	g
Case Style	TO-247AD			

**Ratings and Characteristics Curves**

Figure 1  
Typical Forward Characteristics

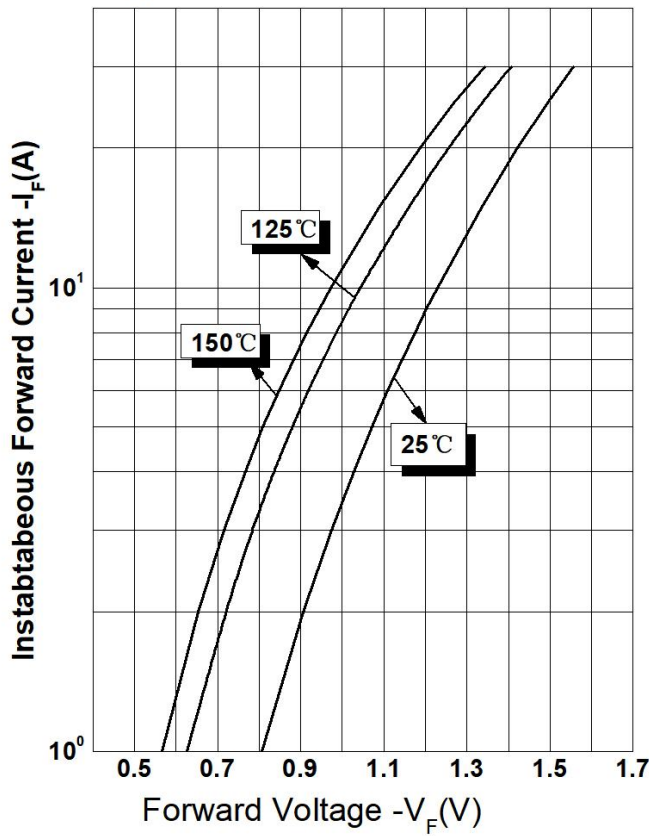


Figure 2  
Typical Reverse Characteristics

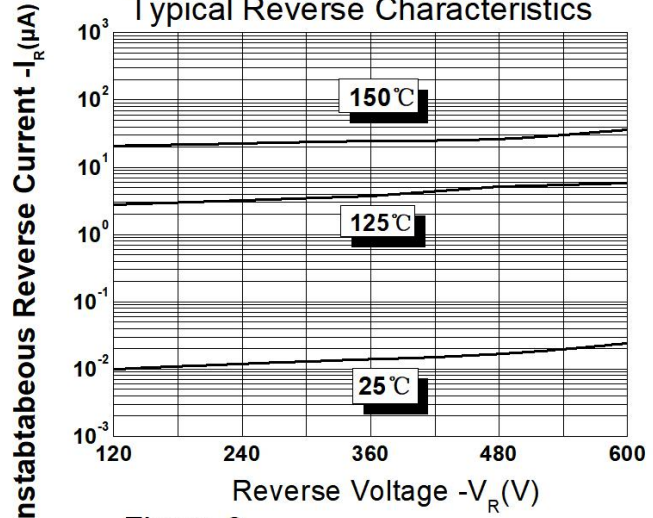
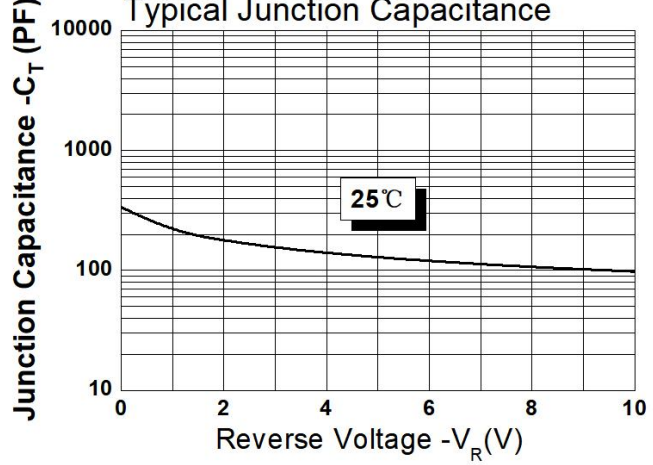
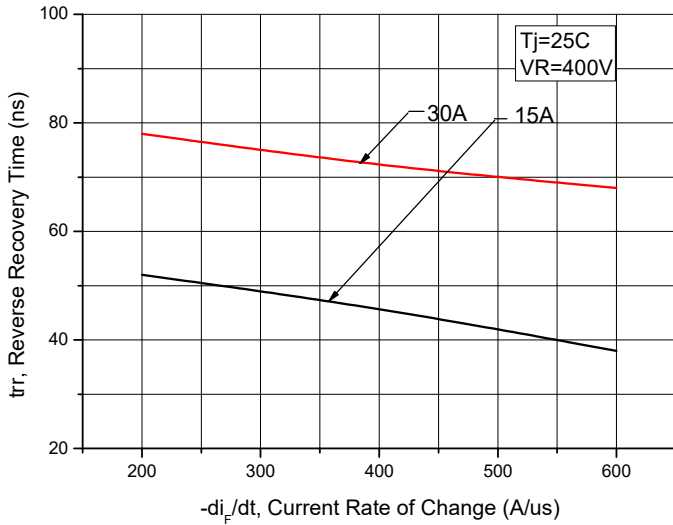
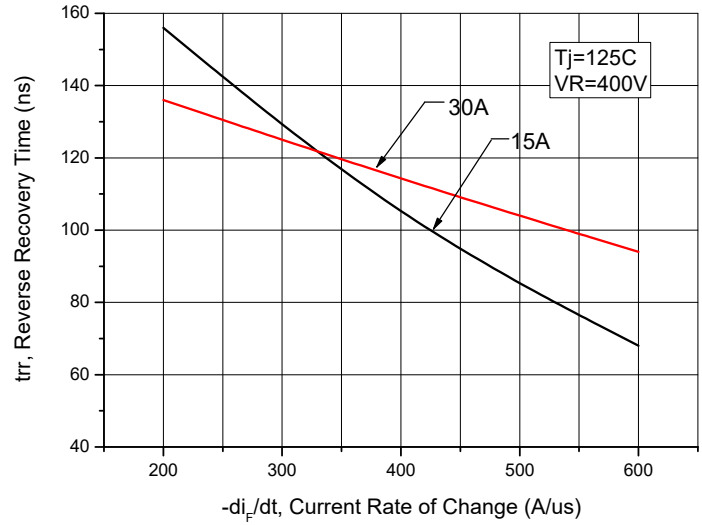


Figure 3  
Typical Junction Capacitance

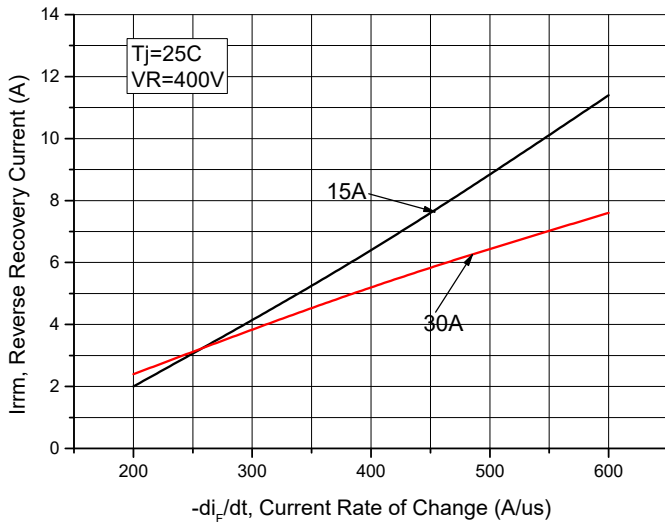




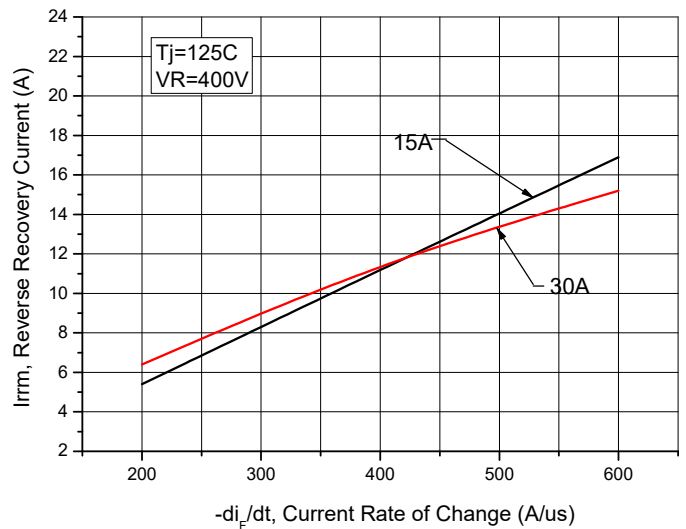
**Figure 4. Reverse Recovery Time vs. Current Rate of Change**



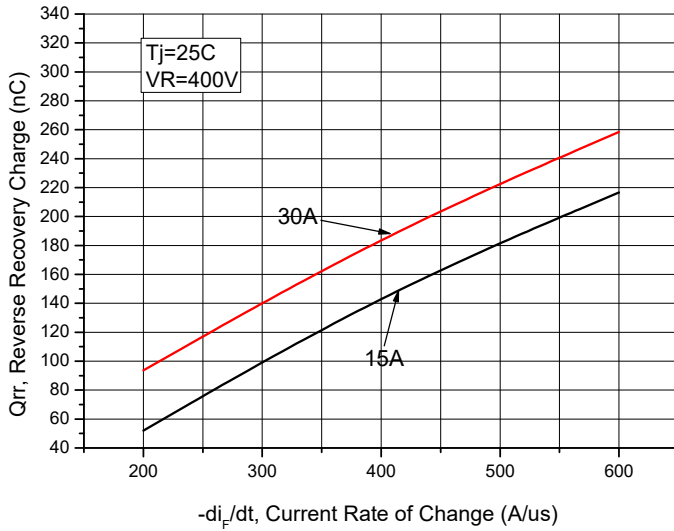
**Figure 5. Reverse Recovery Time vs. Current Rate of Change**



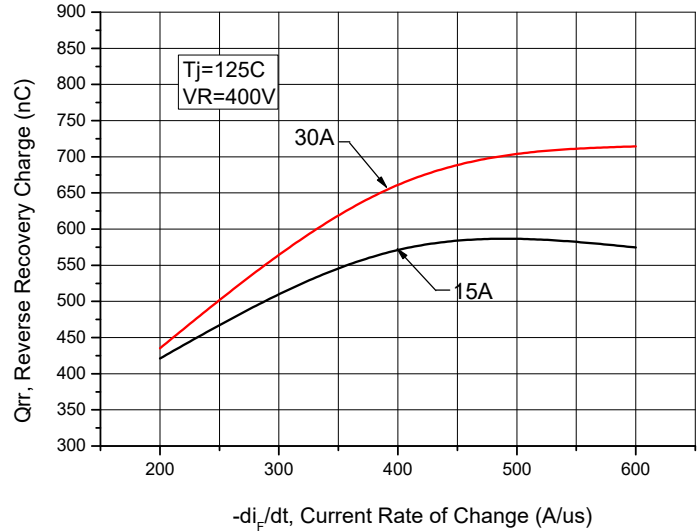
**Figure 6. Reverse Recovery Current vs. Current Rate of Change**



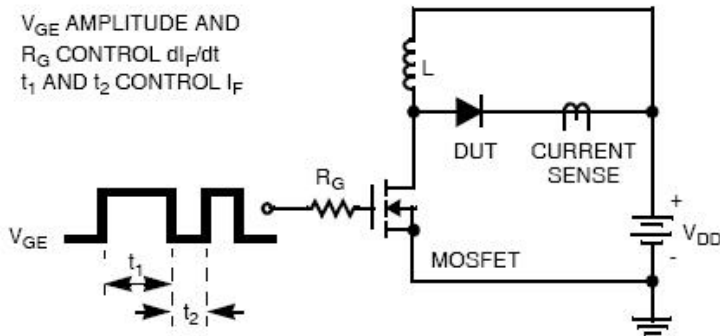
**Figure 7. Reverse Recovery Current vs. Current Rate of Change**



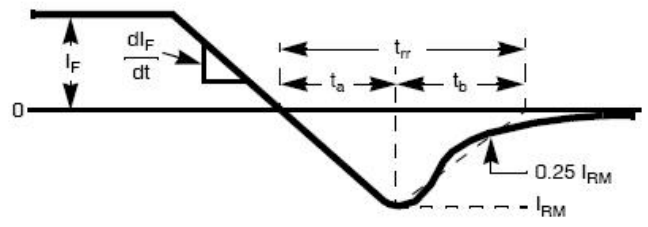
**Figure 8. Reverse Recovery Charge vs. Current Rate of Change**



**Figure 9. Reverse Recovery Charge vs. Current Rate of Change**

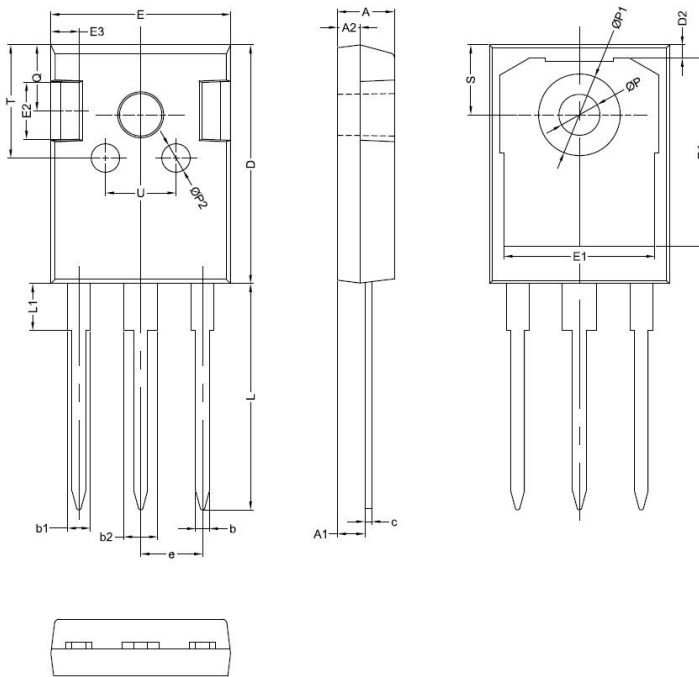


**Figure 10. Diode Test Circuit**



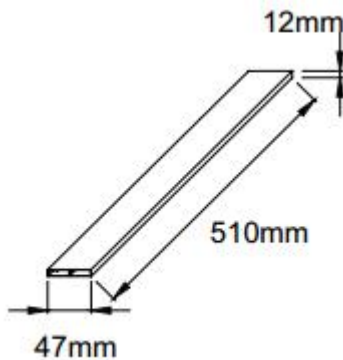
**Figure 11. Diode Reverse Recovery Waveform**

**Mechanical Dimensions TO-247AD**

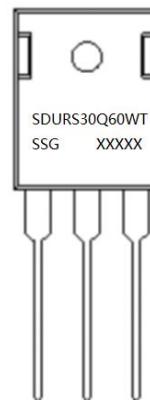


SYMBOL	Millimeters		
	MIN.	TYP.	MAX.
A	4.80	5.00	5.20
A1	2.20	2.41	2.61
A2	1.90	2.00	2.10
b	1.10	1.20	1.40
b1	1.80	2.00	2.20
b2	2.80	3.00	3.20
c	0.50	0.60	0.75
D	20.30	21.00	21.20
D1		16.55	
D2		1.20	
E	15.45	15.80	16.00
E1		13.30	
E2		5.00	
E3		2.50	
e		5.44	
L	19.42	19.92	20.70
L1		4.13	
P	3.50	3.60	3.70
P1	7.1		7.40
P2		2.50	
Q		5.80	
S	6.05	6.15	6.25
T		10.00	
U		6.20	

**Tube Specification**



**Marking Diagram**



Where XXXXX is YYWWL

- SDURS = Device Type
- 30 = Forward Current (30A)
- Q = Q
- 60 = Reverse Voltage (600V)
- WT = Configuration
- SSG = SSG
- YY = Year
- WW = Week
- L = Lot Number

**Cautions:** Molding resin  
Epoxy resin UL:94V-0

**Ordering Information:**

Device	Package	Shipping
SDURS30Q60WT	TO-247AD(Pb-Free)	25pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

- China - Germany - Korea - Singapore - United States •
- <http://www.smc-diodes.com> - [sales@smc-diodes.com](mailto:sales@smc-diodes.com) •

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